



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	16mΩ@10V	19A
	21mΩ@4.5V	
-30V	30mΩ@-10V	-19A
	46mΩ@-4.5V	

Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

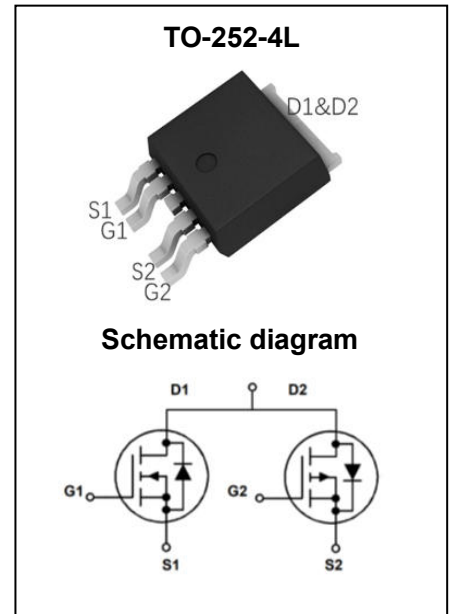
Application

- Power Switching Application

MARKING:



30NP32L = Device Code
XX = Date Code
Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Value	Unit	
Drain - Source Voltage	V_{DS}	30	30	V	
Gate - Source Voltage	V_{GS}	± 20	± 20	V	
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	19	-19	A
	$T_C = 100^\circ\text{C}$	I_D	13	-13	A
Pulsed Drain Current ²	I_{DM}	76	-76	A	
Single Pulsed Avalanche Current ³	I_{AS}	13	-17	A	
Single Pulsed Avalanche Energy ³	E_{AS}	42	72	mJ	
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	30	30	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	50	50	$^\circ\text{C/W}$	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	4.2	4.2	$^\circ\text{C/W}$	
Junction Temperature	T_J	150	150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55~ +150	-55~ +150	$^\circ\text{C}$	

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)
NMOS:

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.65	2.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$		16	32	m Ω
		$V_{GS} = 4.5V, I_D = 5A$		21	42	
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 8A$		20		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		475		pF
Output Capacitance	C_{oss}			65		
Reverse Transfer Capacitance	C_{rss}			48		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.6		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 15V, V_{GS} = 10V, I_D = 5A$		10		nC
Gate-source Charge	Q_{gs}			1.8		
Gate-drain Charge	Q_{gd}			1.8		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 10V, R_L = 1.87\Omega$ $R_G = 3\Omega$		5		ns
Turn-on Rise Time	t_r			3		
Turn-off Delay Time	$t_{d(off)}$			15		
Turn-off Fall Time	t_f			3		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.2	V

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

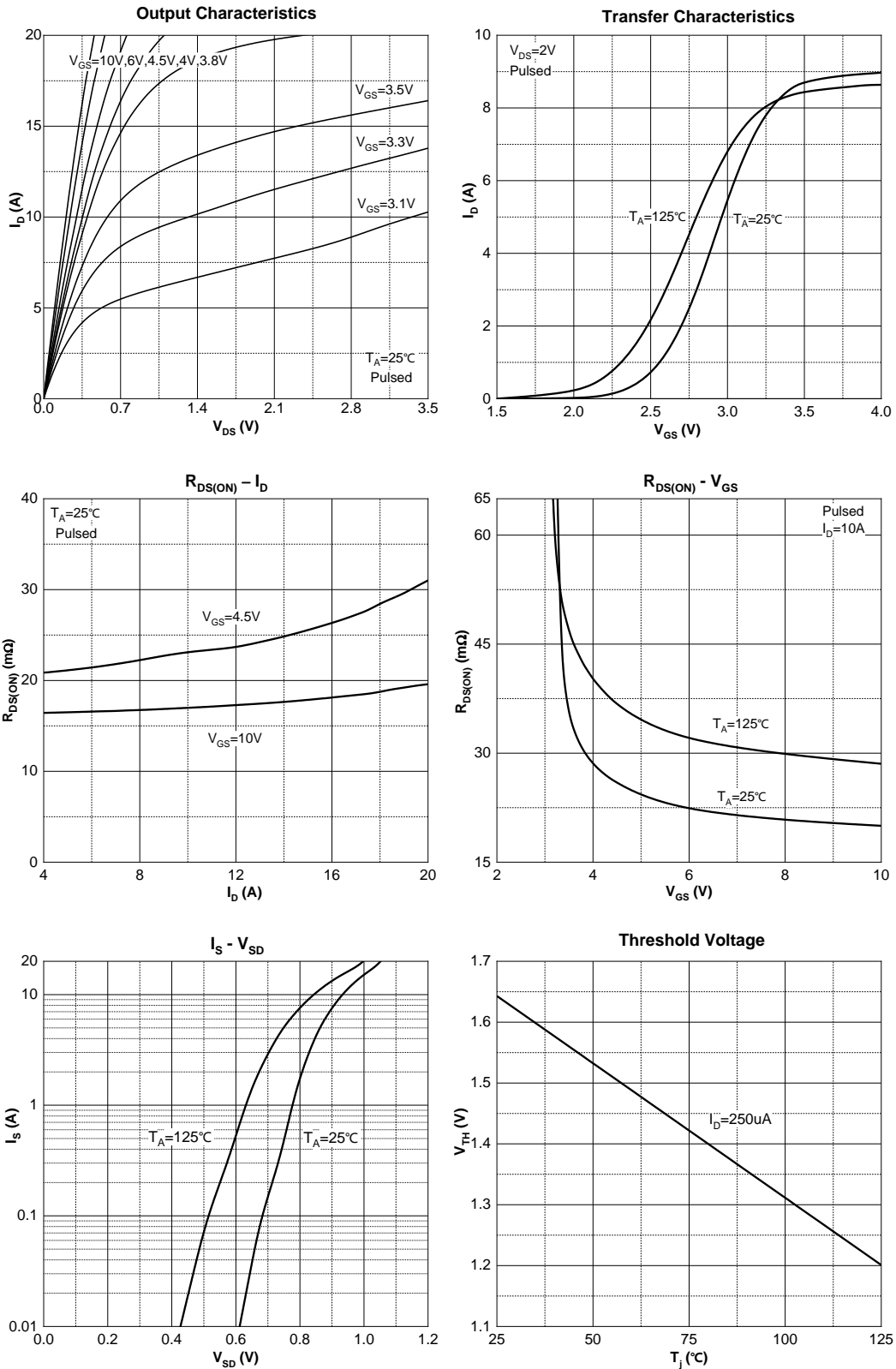
PMOS:

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.7	-2.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -5A$		30	40	m Ω
		$V_{GS} = -4.5V, I_D = -5A$		46	70	
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -12A$		20		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		915		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			88		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		36.4		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V, I_D = -5A$		10.7		nC
Gate-source Charge	Q_{gs}			1.0		
Gate-drain Charge	Q_{gd}			1.4		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V,$ $R_L = 1.25\Omega, R_G = 3\Omega$		9		ns
Turn-on Rise Time	t_r			6		
Turn-off Delay Time	$t_{d(off)}$			20		
Turn-off Fall Time	t_f			7		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = -10A$			-1.2	V

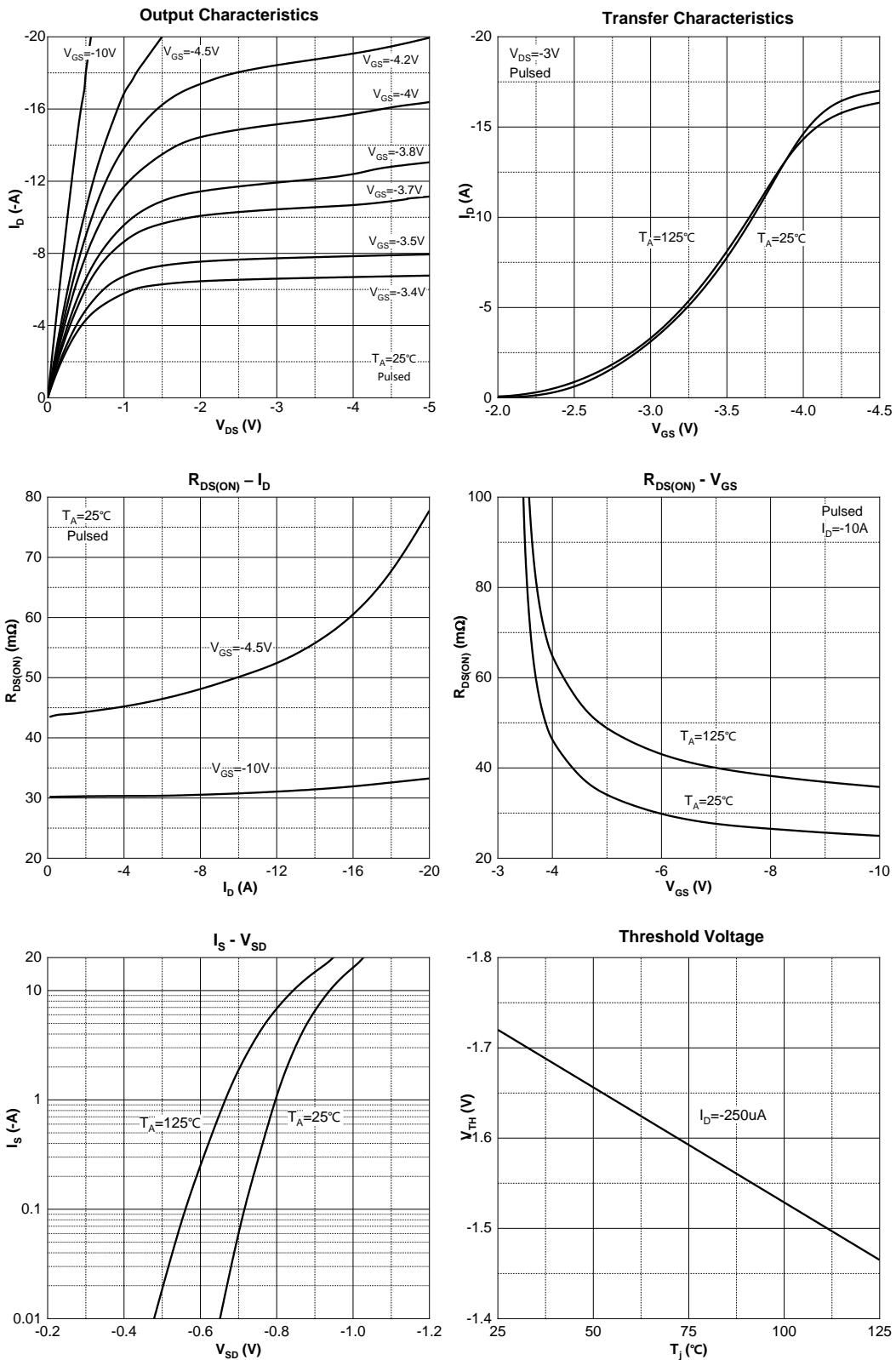
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = \pm 15V, V_{GS} = \pm 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

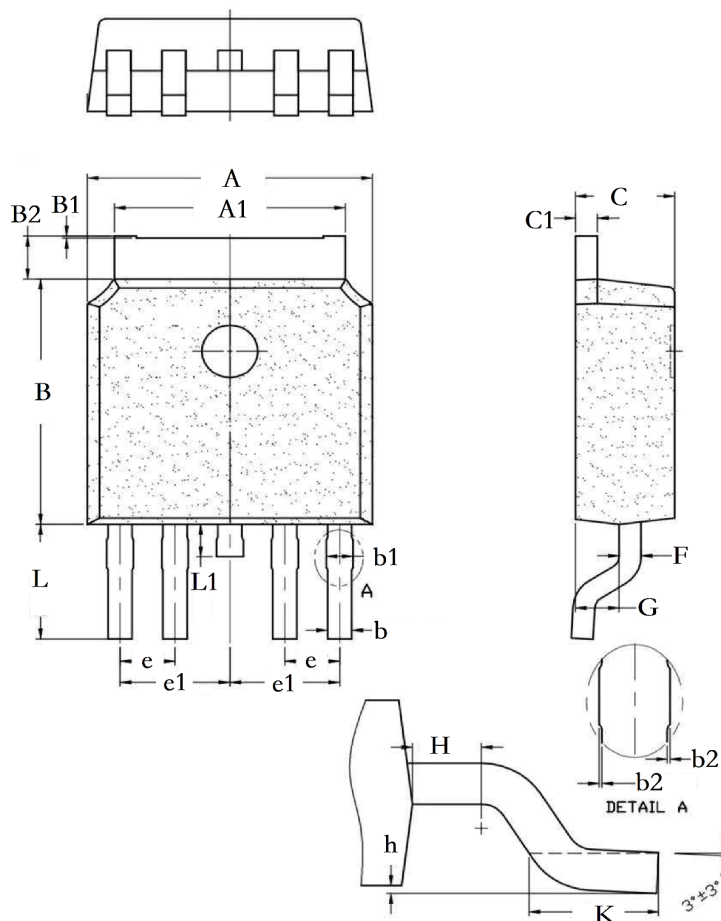
Typical Characteristics



Typical Characteristics



TO-252-4L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	6.550	6.650	0.258	0.262
A1	5.234	5.434	0.206	0.214
B	6.050	6.150	0.238	0.242
B1	0.000	0.050	0.000	0.002
B2	0.962	1.162	0.038	0.046
C	2.250	2.350	0.089	0.093
C1	0.458	0.558	0.018	0.022
L	2.698	2.998	0.106	0.118
L1	0.700	0.900	0.028	0.035
b	0.510	0.610	0.020	0.024
b1	0.570	0.670	0.022	0.026
b2	0.000	0.050	0.000	0.002
e	1.270TYP		0.050TYP	
e1	2.540TYP		0.100TYP	
F	0.458	0.558	0.018	0.022
G	0.960	1.06	0.038	0.042
H	0.650	0.950	0.026	0.037
h	0.050	0.150	0.002	0.006
K	1.300	1.700	0.051	0.067